

L Number	Hits	Search Text	DB	Time stamp
-	3	"6150696"	USPAT	2004/09/17 12:57
-	27	((("6306729") or ("6291315") or ("6232201") or ("5854500") or ("6110391") or ("EP793263A2") or ("6004860") or ("5426073") or ("6150696") or ("6294478") or ("6326279") or ("20020025652A1") or ("6350702") or ("6214702") or ("EP854500A") or ("JP8274285A") or ("JP8274286A") or ("5811348") or ("6127281") or ("4597060A") or ("3874920A")).PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/09/16 14:35
-	1	1990-109204.NRAN.	DERWENT	2004/09/16 14:24
-	18	"5426073"	USPAT; US-PGPUB	2004/09/16 14:41
-	8	"1158581"	EPO; DERWENT	2004/09/16 15:03
-	4	"6232201"	USPAT; US-PGPUB	2004/09/16 15:32
-	524	438/458.ccls.	USPAT; US-PGPUB	2004/09/16 16:36
-	659	438/455.ccls. not (438/458.ccls.)	USPAT; US-PGPUB	2004/09/16 16:59
-	202	438/406.ccls. not (438/455.ccls. 438/458.ccls.)	USPAT; US-PGPUB	2004/09/16 17:22
-	1835	257/347.ccls. not (438/406.ccls. 438/455.ccls. 438/458.ccls.)	USPAT; US-PGPUB	2004/09/16 19:23
-	1101	((rapid adj thermal) rta) with (passivat\$5 insulat\$5 protect\$5 dielectric\$1) with (layer film)	USPAT; US-PGPUB	2004/09/17 15:25
-	140	((rapid adj thermal) rta) with (passivat\$5 insulat\$5 protect\$5 dielectric\$1) with (layer film)) and (silicon\$lon\$insulator soi)	USPAT; US-PGPUB	2004/09/16 19:38
-	97	wafer with (anneal\$5 rapid\$1thermal rta) with passivat\$5	USPAT; US-PGPUB	2004/09/17 13:40
-	1	stabox	USPAT; US-PGPUB	2004/09/17 13:40
-	10	wafer with oxidiz\$7 with (rapid\$1thermal RTA)	USPAT; US-PGPUB	2004/09/17 14:11
-	1	"6624047"	USPAT; US-PGPUB	2004/09/17 14:16
-	0	((silicon\$lon\$insulator) soi) and ((rapid\$1thermal RTA) with passivat\$5 with encapsulat\$5)	USPAT; US-PGPUB	2004/09/17 14:19
-	0	((silicon\$lon\$insulator) soi) and ((rapid\$1thermal RTA) with passivat\$5)	USPAT; US-PGPUB	2004/09/17 14:20
-	1400	(silicon\$lon\$insulator soi) and (passivat\$5 near (film layer))	USPAT; US-PGPUB	2004/09/17 14:23
-	143	((silicon\$lon\$insulator soi) and (passivat\$5 near (film layer))) and (rapid\$1thermal RTA)	USPAT; US-PGPUB	2004/09/17 14:24
-	248	((rapid adj thermal) rta) with (passivat\$5 insulat\$5 protect\$5 dielectric\$1) with (layer film)	EPO; JPO; DERWENT; IBM_TDB	2004/09/17 15:26
-	6	((rapid adj thermal) rta) with (passivat\$5 insulat\$5 protect\$5 dielectric\$1) with (layer film)) and (silicon\$lon\$insulator soi)	EPO; JPO; DERWENT; IBM_TDB	2004/09/17 15:26
-	256	SOI and smart\$1cut	USPAT; US-PGPUB	2004/09/18 00:23
-	154	SOI and smart\$1cut and bonding	USPAT; US-PGPUB	2004/09/18 00:23
-	49	(SOI and smart\$1cut and bonding) and separating	USPAT; US-PGPUB	2004/09/18 00:32
-	2	(rapid\$1thermal\$1anneal\$5 RTA) with temperature with minute\$1 with oxid\$7	USPAT; US-PGPUB	2004/09/18 00:34